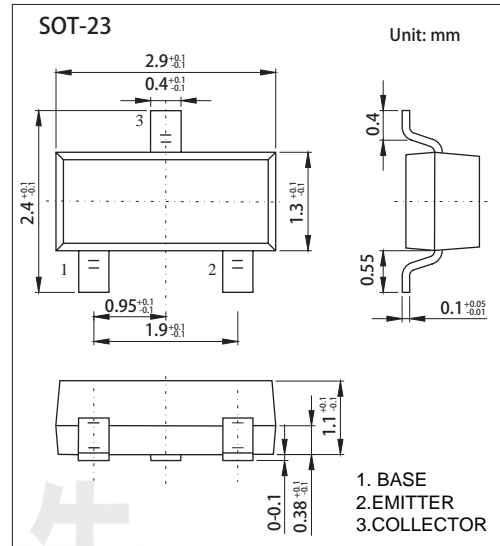


Transistor

PNP Transistors 2SA1015

■ Features

- High voltage and high current
- Excellent hFE Linearity
- Low noise
- Complementary to 2SC1815



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|---|------------------|------------|------|
| Collector - Base Voltage | V _{CB0} | -50 | V |
| Collector - Emitter Voltage | V _{CE0} | -50 | |
| Emitter - Base Voltage | V _{EB0} | -5 | |
| Collector Current - Continuous | I _c | -150 | mA |
| Collector Power Dissipation | P _c | 200 | mW |
| Thermal Resistance From Junction To Ambient | R _{θJA} | 625 | °C/W |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{stg} | -55 to 150 | |

PNP Transistors 2SA1015

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|------|------|
| Collector- base breakdown voltage | V _{CB0} | I _C = -100 μA, I _E =0 | -50 | | | V |
| Collector- emitter breakdown voltage | V _{CE0} | I _C = -0.1 mA, I _B =0 | -50 | | | |
| Emitter - base breakdown voltage | V _{EB0} | I _E = -100 μA, I _C =0 | -5 | | | |
| Collector cut-off current | I _{CBO} | V _{CB} = -50 V, I _E =0 | | | -0.1 | μA |
| Collector cut-off current | I _{CEO} | V _{CE} = -50 V, I _B =0 | | | -0.1 | |
| Emitter cut-off current | I _{EBO} | V _{EB} = -5V, I _C =0 | | | -0.1 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =-100 mA, I _B = -10mA | | | -0.3 | V |
| Base - emitter saturation voltage | V _{BE(sat)} | I _C =-100 mA, I _B = -10mA | | | -1.1 | |
| DC current gain | h _{FE} | V _{CE} = -6V, I _C = -2mA | 130 | | 400 | |
| Transition frequency | f _T | V _{CE} = -10V, I _C = -1mA, f=30MHz | 80 | | | MHz |

■ Classification of h_{FE}

| Rank | L | H |
|---------|---------|---------|
| Range | 130-200 | 200-400 |
| Marking | BA | |